

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max $T_A = +25^\circ\text{C}$
60V	2Ω @ $V_{GS} = 10\text{V}$	380mA
	3Ω @ $V_{GS} = 5\text{V}$	310mA

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Power Management Functions
- Backlighting

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected Up To 2kV**
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208 [Ⓔ]
- Weight: 0.008 grams (approximate)

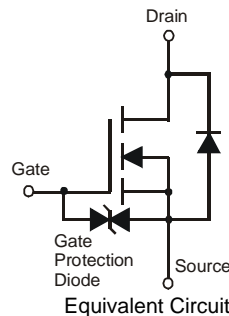


ESD protected up to 2kV

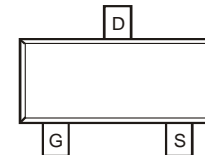


SOT23

Top View



Equivalent Circuit



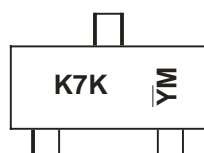
Top View

Ordering Information (Note 4)

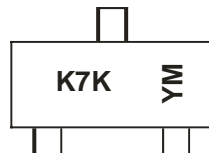
Part Number	Compliance	Case	Packaging
2N7002K-7	Standard	SOT23	3000/Tape & Reel
2N7002KQ-7	Automotive	SOT23	3000/Tape & Reel
2N7002K-13	Standard	SOT23	10000/Tape & Reel
2N7002KQ-13	Automotive	SOT23	10000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>

Marking Information



Chengdu A/T Site



Shanghai A/T Site

K7K = Product Type Marking Code
 YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)
 ȲM = Date Code Marking for CAT (Chengdu Assembly/ Test site)
 Y or Ȳ = Year (ex: A = 2013)
 M = Month (ex: 9 = September)

Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	T	U	V	W	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	380 300	mA
	t < 5s	T _A = +25°C T _A = +70°C	I _D	430 340	mA
Continuous Drain Current (Note 6) V _{GS} = 5V	Steady State	T _A = +25°C T _A = +70°C	I _D	310 240	mA
	t < 5s	T _A = +25°C T _A = +70°C	I _D	350 270	mA
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	0.5	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%) (Note 6)			I _{DM}	1.2	A

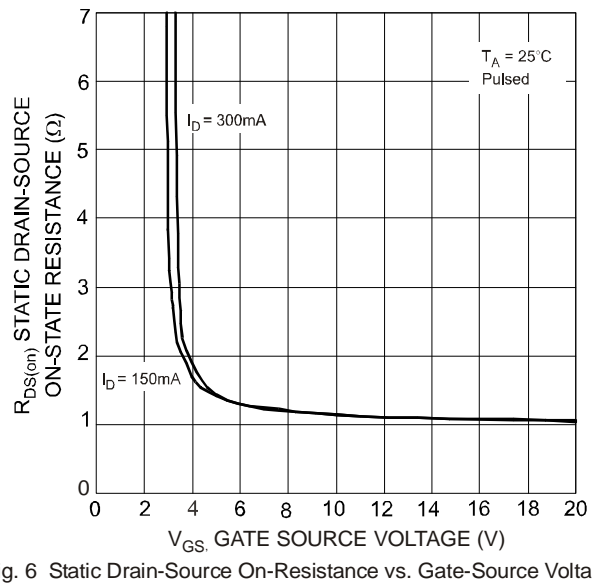
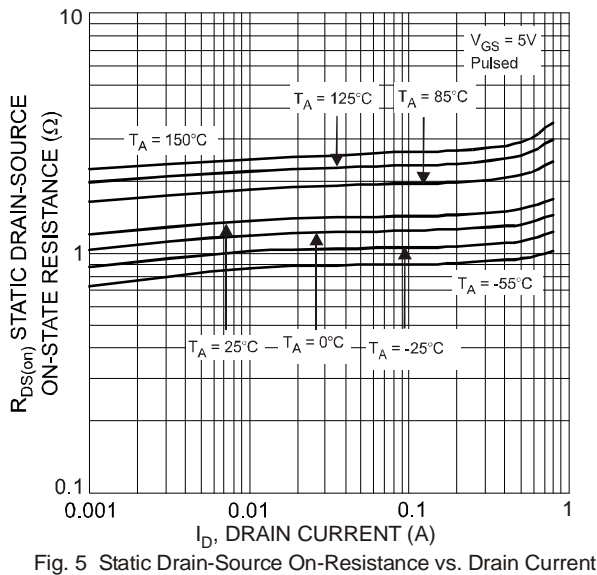
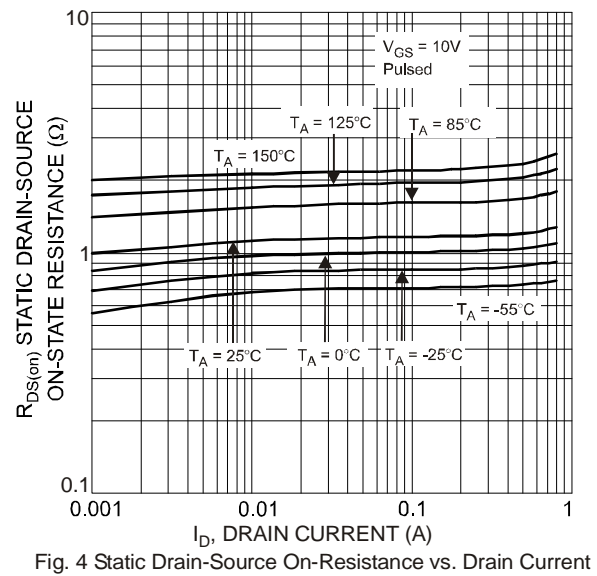
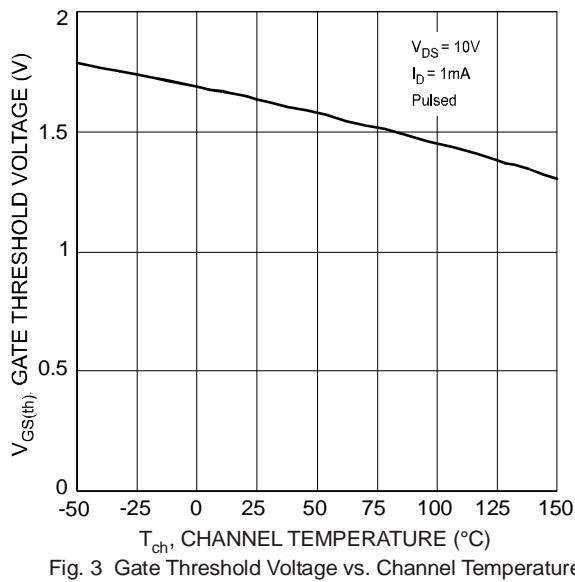
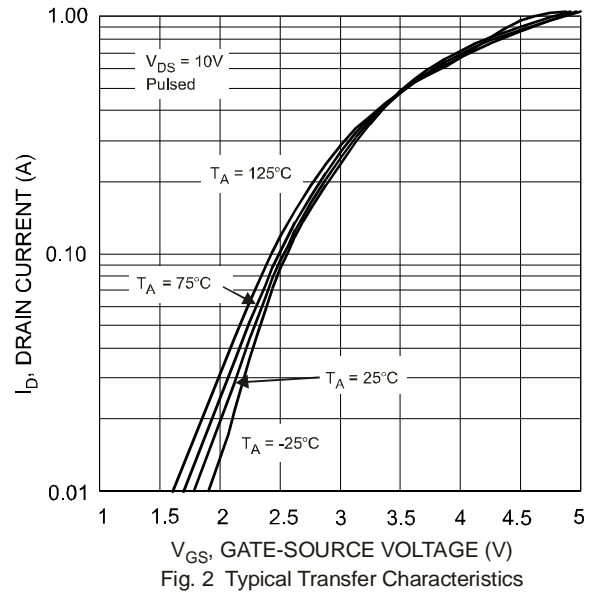
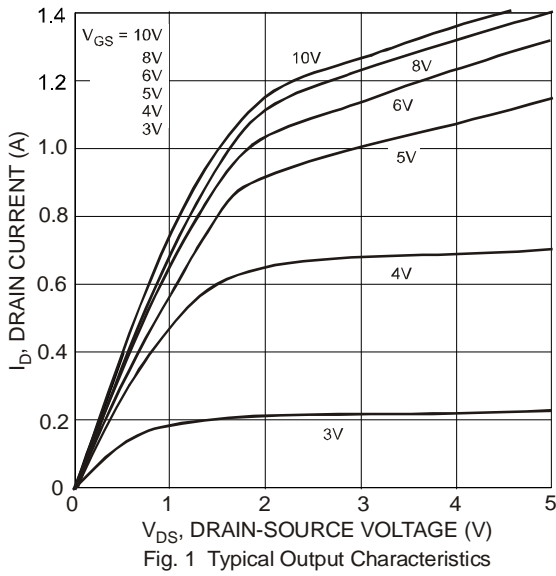
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P _D	370	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	357	°C/W
	t < 5s		292	
Total Power Dissipation (Note 6)		P _D	540	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	240	°C/W
	t < 5s		197	
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	91	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 10μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	1.0	1.6	2.5	V	V _{DS} = 10V, I _D = 1mA
Static Drain-Source On-Resistance	R _{DS(on)}	—	—	2.0	Ω	V _{GS} = 10V, I _D = 0.5A
		—	—	3.0		V _{GS} = 5V, I _D = 0.05A
Forward Transfer Admittance	Y _{fs}	80	—	—	ms	V _{DS} = 10V, I _D = 0.2A
Diode Forward Voltage	V _{SD}	—	0.75	1.1	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	30	50	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	4.2	25	pF	
Reverse Transfer Capacitance	C _{rss}	—	2.9	5.0	pF	
Gate Resistance	R _g	—	133	—	Ω	f = 1MHz, V _{GS} = 0V, V _{DS} = 0V
Total Gate Charge	Q _g	—	0.3	—	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 250mA
Gate-Source Charge	Q _{gs}	—	0.2	—	nC	
Gate-Drain Charge	Q _{gd}	—	0.08	—	nC	
Turn-On Delay Time	t _{D(on)}	—	3.9	—	ns	V _{DD} = 30V, V _{GS} = 10V, R _G = 25Ω, I _D = 200mA
Turn-On Rise Time	t _r	—	3.4	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	15.7	—	ns	
Turn-Off Fall Time	t _f	—	9.9	—	ns	

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout
 - Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.



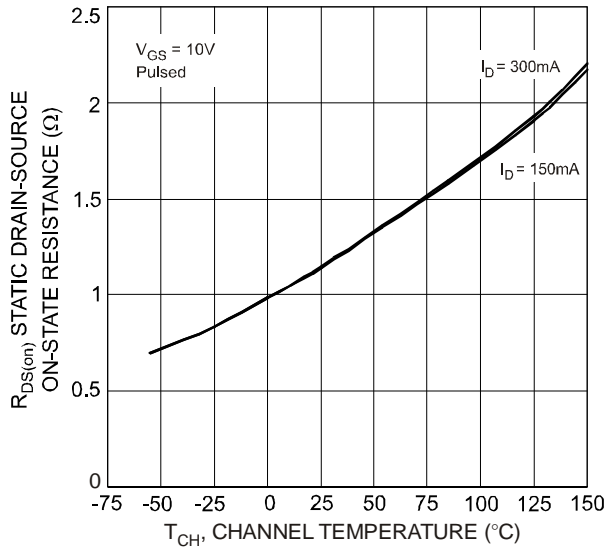


Fig. 7 Static Drain-Source On-State Resistance vs. Channel Temperature

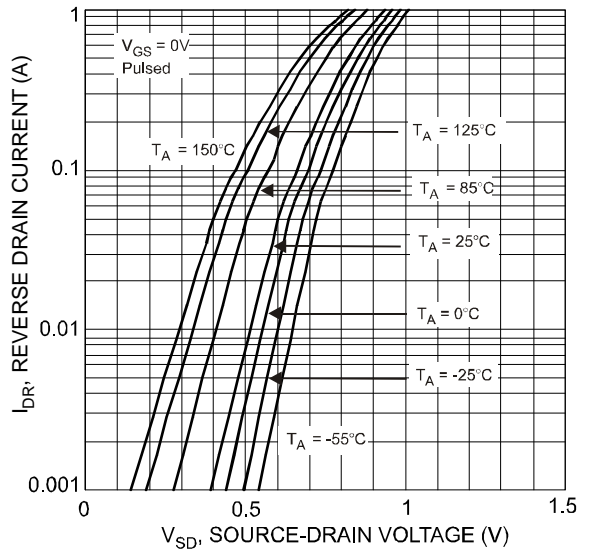


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

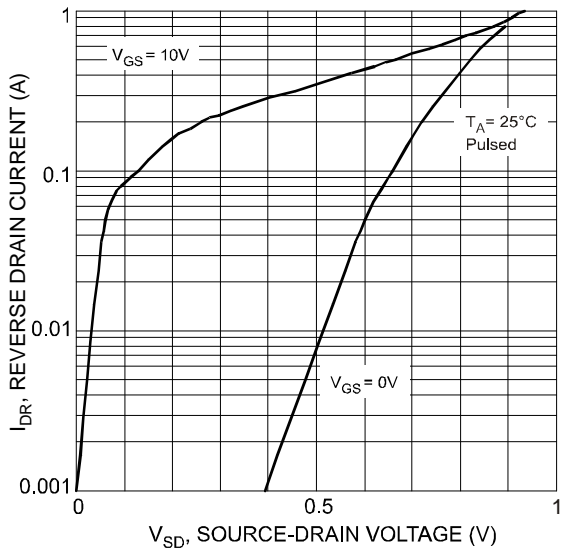


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage

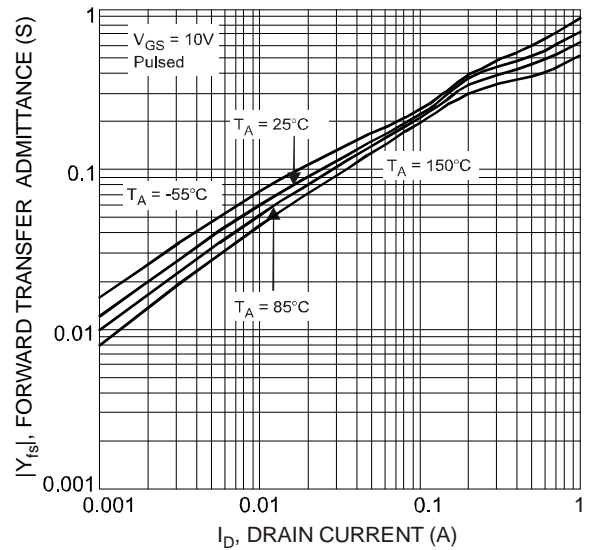


Fig. 10 Forward Transfer Admittance vs. Drain Current

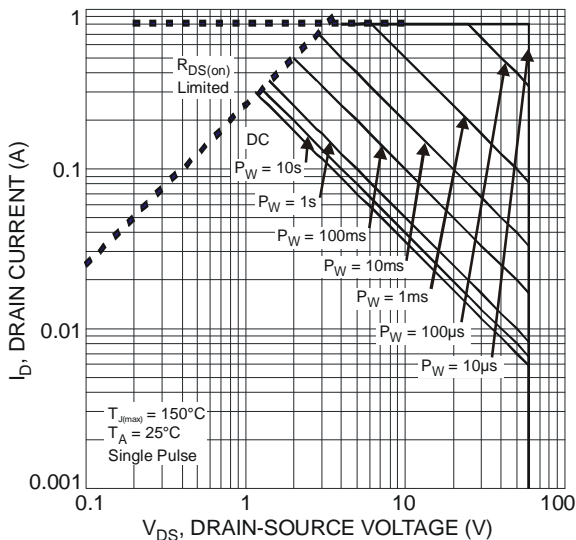


Fig. 11 Safe Operation Area

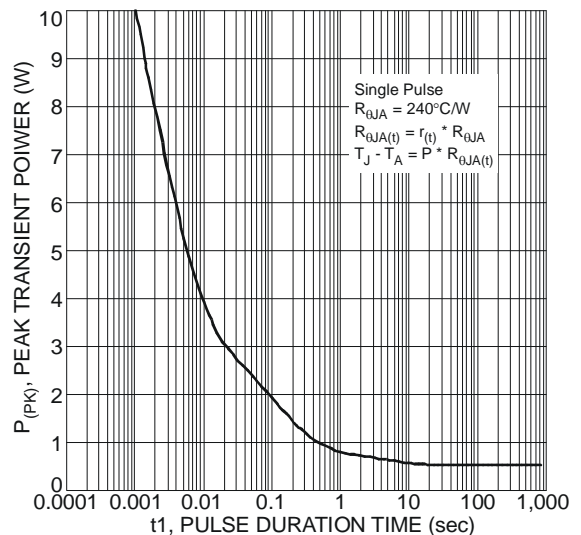
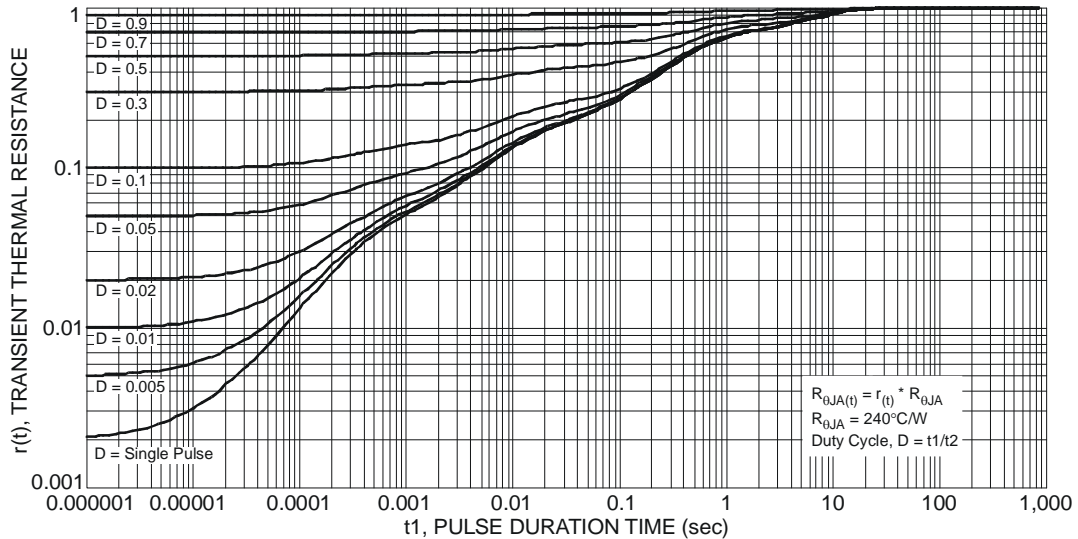
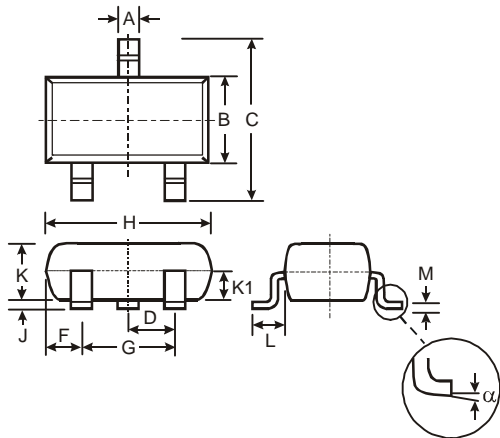


Fig. 12 Single Pulse Maximum Power Dissipation



Package Outline Dimensions

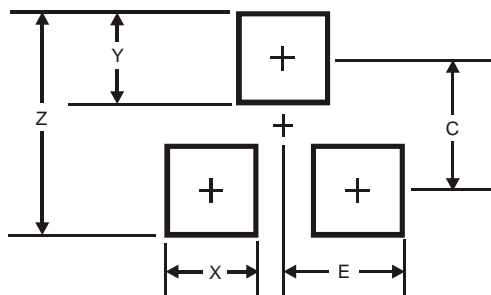
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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